Receipt date: 01/22/2008

	2 5 500A R			
Form PTO 1449	JAN	ATTY, DOCKET NUMBER HIRA.0236	Serial Number 10/591,947	
U.S. Department Corporation		APPLICANT YUASA		
Information Disclosure Statement by Applicant		FILING DATE September 8, 2006	GROUP 2827	

U.S. Patent Documents

Examiner	DOCUMENT NUMBER	DATE	Name	CLASS	SUB	FILING DATE
Initial					CLASS	
	2007/0128470	6/7/2007	Nagahama et al.			2/12/2007
	2004/0144995	7/29/2004	Nagahama et al.			5/24/2002
	2004/0245553	12/9/2004	Hosomi et al.			4/8/2003
	2006/0056115	3/16/2006	Djayaprawira et al.			9/7/2005

Foreign Patent Documents

Examiner	DOCUMENT NUMBER	UMBER FILING DATE	COUNTRY	CLA	Sun-	TRANSLATION	
Initial				ss	CLASS	YES	No
	2003-318465*	4/23/2002	Japan			Abstract	
	WO 2002/099905	5/24/2002	PCT			Abstract	
	EP 1 391 942	5/24/2002	EP			x	
	2002-204004	12/28/2000	Japan	1		Abstract	X
	2002-289943	3/26/2001	Japan			Abstract	X
	2003-304010**	4/9/2002	Japan			Abstract	
	WO 2003/085750	4/8/2003	PCT			Abstract	
	EP 1 494 295 .	4/8/2003	EP			X	
100	2006-080116***	9/7/2004	Japan			Abstract	

- Corresponds to U.S. Patent 2007/0128470, U.S. Patent 2004/0144995, WO2002/099905, and EPI 391 942, listed above.
- ** Corresponds to U.S. Patent 2004/0245553, WO 2003/085750, and EP 1 494 295, listed above.
- *** Corresponds to U.S. Patent 2006/0056115, listed above.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /AC/ (10/26/2009)

Receipt date: 01/22/2008

Wolf, S.A. et al., "Spintronics: A Spin-Based Electronics Vision for the Future", Science, Vol. 294, dovember 16, 2001, pp. 1488-1495. Wulfhekel, W. et al., "Single-Crystal Magnetotunnel Junctions", Applied Physics Letters, Vol. 78, No. 4,					
Nulfhekel, W. et al., "Single-Crystal Magnetotunnel Junctions", Applied Physics Letters, Vol. 78, No. 4,					
lanuary 22, 2001, pp. 509-511					
Julliere, M., "Tunneling Between Ferromagnetic Films", Physics Letters, Vol. 54A, No. 3, September 8, 1975, pp.225-226.					
Soulen, R.J, Jr. et al., "Measuring the Spin Polarization of a Metal with a Superconducting Point Contact", Science, Vol. 282, October 2, 1998, pp. 85-88.					
Saito, Y. et al., "Correlation between Barrier Width, Barrier Height, and DC Bias Voltage Dependences on the Magnetoresistance Ratio in Ir-Mn Exchange Biased Single and Double Tunnel Junctions", Jpn. J. Appl. Phys., Vol. 39 (2000), pp. 1.1035-L.138.					
lura, S. et al., "Enhancement of Thermal Stability in Ferromagnetic Tunnel Junctions Prepared by the Radical Oxidation Method", Journal of the Magnetics Society of Japan, Vol. 26, No. 6 (2002), pp. 839-842, abstract only in English.					
Bowen, M. et al., "Large Magnetoresistance in Fe/MgO/FeCo(001) Epitaxial Tunnel Junctions on GaAs(001)", Applied Physics Letters, Vol. 79, No. 11, September 10, 2001, pp. 1655-1657.					
Simmons, John G., "Generalized Formula for the Electric Tunnel Effect between Similar Electrodes Separated by a Thin Insulating Film", Journal of Applied Physics, Vol. 34, NO. 6, June 1963, pp. 1793-1803.					
Vassent, J.L. et al., "A Study of Growth and the Relaxation of Elastic Strain in MgO on Fe(001)", J. Appl. Phys. Vol. 80, No. 10, November 15, 1996, pp. 5727-5735.					
Faure-Vincent, J. et al., "High Tunnel Magnetoresistance in Expitaxial Fe/MgO/Fe Tunnel Junctions", Applied Physics Letters, Vol. 82, No. 25, June 23, 2003, pp. 4507-4509.					
Meyerheim, H.L. et al., "Geometrical and Compositional Structure at Metal-Oxide Interfaces: MgO on Fc(001)", Physical Review Letters, Vol. 18, No. 7, August 13, 2001, pp. 076102-1 – 076102-4.					
Butler, W.H. et al., "Spin-dependent Tunncling Conductance of Fe[MgO]Fe Sandwiches", Physical Review B., Vol. 63, 054416, 2001, pp. 054416-1 – 054416-12.					
Mathon, J. et al., "Theory of Tunneling Magnetoresistance of an Epitaxial Fe/MgO/Fe(001) Junction", Physical Review B., Vol. 63, 220403(R), 2001, pp. 220403-1 – 220403-4. Zhang, XG. et al., "Effects of the Iron-Oxide Layer in Fe-FeO-MgO-Fe Tunneling Junctions", Physical Review B, Vol. 68, 092402, 2003, pp. 092402-1 – 092402-4. Zhang, XG. et al., "Large Magnetoresistance in bec Co/MgO/Co and FeCo/MgO/FeCo Tunnel Junctions", Physical Review B, Vol. 70, 172407, 2004, pp. 172407-1 – 172407-4. Gibson, A. et al., "Stability of Vacancy Defects in MgO: The Role of Charge Neutrality", Physical Review B, Vol. 50, No. 4, July 15, 1994-11, pp. 2582-2592.					
					Yuasa, S. et al., "High Tunnel Magnetoresistance at Room Temperature in Fully Expinaxial Fe/MgO/Fe Tunnel Junctions Due to Coherent Spin-Polarized Tunneling", Japanese Journal of Applied Physics, Vol. 43 No. 4B, 2004, pp. L5884-L509.
					Alonzo Chambliss/ (10/26/2009) DAYE COHSIDERED
S S S E I I E E I I E E I I E E I E E E E					

PTO1449

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /AC/ (10/26/2009)

citation if not in conformance and not considered. Include copy of this form with next communication to applicant